



TEXAS
INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS090

查询CD4572UB供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

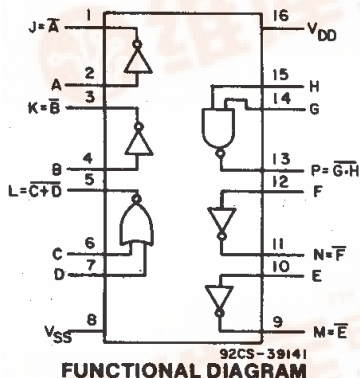
CD4572UB Types

CMOS Hex Gate

Four Inverters, One 2-Input NOR Gate, One 2-Input NAND Gate

Features:

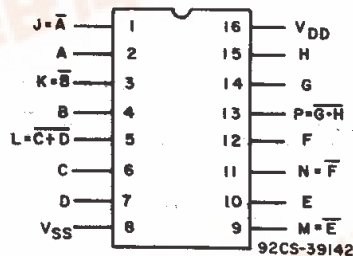
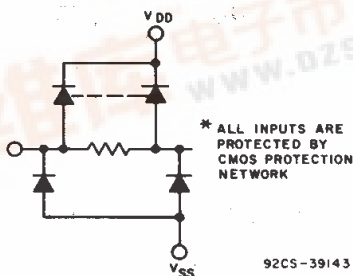
- Pin 7 NOR input positioned adjacent to V_{SS} for easy use of gate as an inverter
- Pin 15 NAND input positioned adjacent to V_{DD} for easy use of gate as an inverter
- Standard symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range: 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



■ CD4572UB Hex Gate provides the system designer with direct implementation of inverter, NAND, and NOR functions and supplements the existing family of CMOS gates.

The CD4572UB devices meet all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices."

The CD4572UB types are supplied in 16-lead dual-in-line ceramic packages (D and F suffixes), a 16-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).



TERMINAL ASSIGNMENT

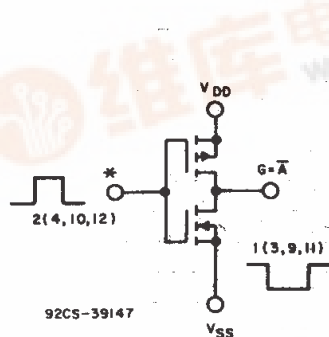


Fig. 1 - Schematic diagram of one of four identical inverters.

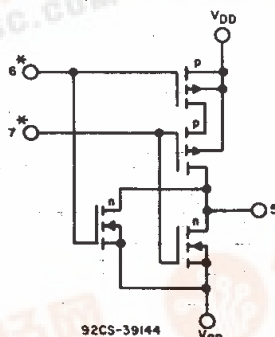


Fig. 2 - Schematic diagram for the 2-input NOR gate.

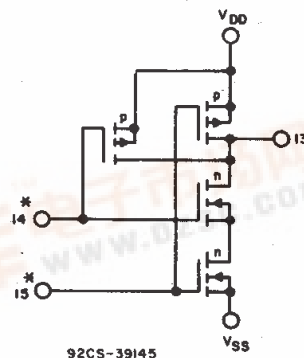


Fig. 3 - Schematic diagram for the 2-input NAND gate.

CD4572UB Types

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal

INPUT VOLTAGE RANGE, ALL INPUTS

DC INPUT CURRENT, ANY ONE INPUT

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^{\circ}\text{C}$ to $+100^{\circ}\text{C}$

For $T_A = +100^{\circ}\text{C}$ to $+125^{\circ}\text{C}$

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$

OPERATING-TEMPERATURE RANGE (T_A)

STORAGE TEMPERATURE RANGE (T_{stg})

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79\text{mm}$) from case for 10s max

-0.5V to +20V

-0.5V to $V_{DD} + 0.5\text{V}$

$\pm 10\text{mA}$

500mW

Derate Linearly at $12\text{mW}/^{\circ}\text{C}$ to 200mW

100mW

-55°C to $+125^{\circ}\text{C}$

-65°C to $+150^{\circ}\text{C}$

$+265^{\circ}\text{C}$

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For $T_A = \text{Full Package-Temperature Range}$)	3	18	V

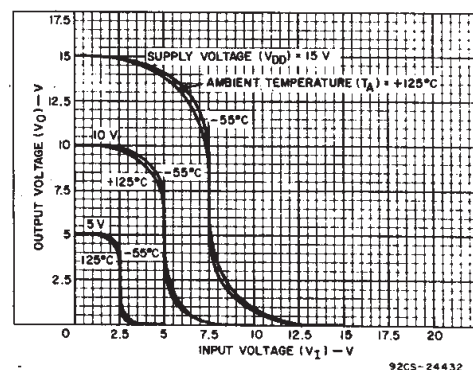
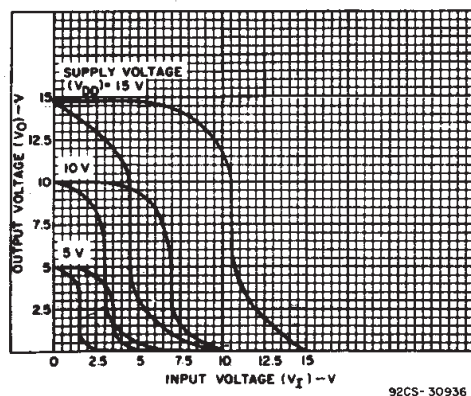
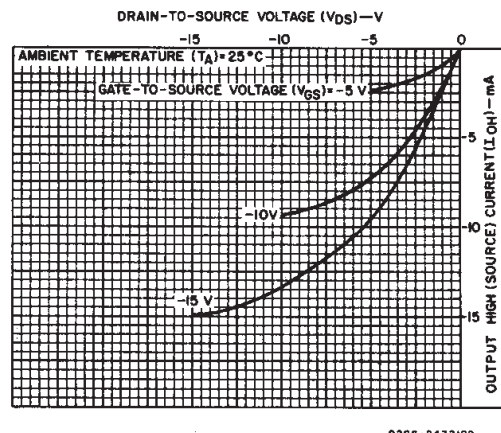
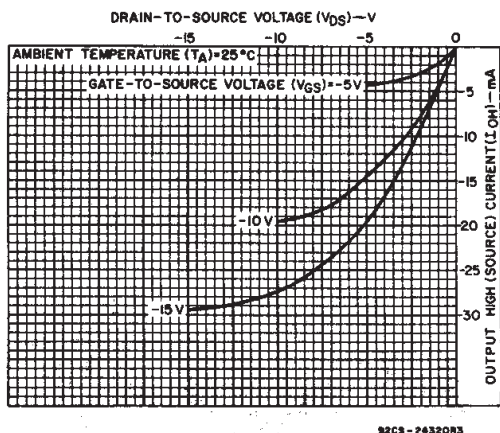
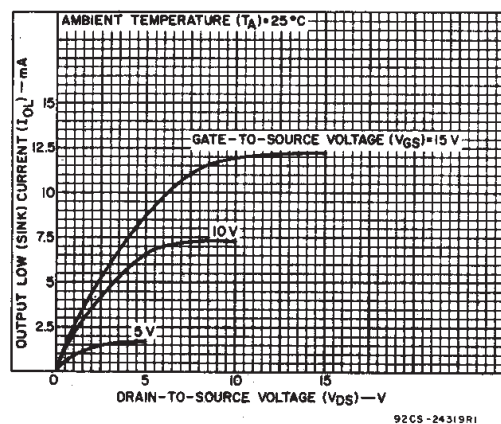
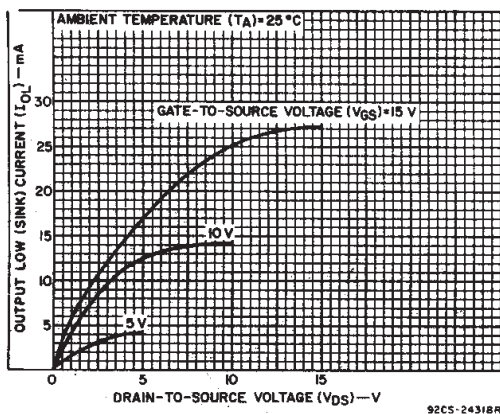
STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)								
				-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0, 5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0, 10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0, 15	15	1	1	30	30	—	0.01	1	
	—	0, 20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0, 5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0, 10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0, 15	15	4.2	4	2.8	2.4	3.4	6.8	—	
	4.6	0, 5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	
Output High (Source) Current, I _{OH} Min.	2.5	0, 5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	mA
	9.5	0, 10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0, 15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
	—	0, 5	5	0.05				—	0	0.05	
Output Voltage: Low-Level, V _{OL} Max.	—	0, 10	10	0.05				—	0	0.05	
	—	0, 15	15	0.05				—	0	0.05	
	—	0, 5	5	4.95				4.95	5	—	
Output Voltage: High-Level, V _{OH} Min.	—	0, 10	10	9.95				9.95	10	—	
	—	0, 15	15	14.95				14.95	15	—	
	0.5, 4.5	—	5	1				—	—	1	
Input Low Voltage, V _{IL} Max.	1, 9	—	10	2				—	—	2	
	1.5, 13.5	—	15	2.5				—	—	2.5	
Input High Voltage, V _{IH} Min.	0.5, 4.5	—	5	4				4	—	—	
	1, 9	—	10	8				8	—	—	
	1.5, 13.5	—	15	12.5				12.5	—	—	
Input Current, I _{IN} Max.	—	0, 18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

CD4572UB Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
		V_{DD} (V)	Min.	Typ.	Max.	
Propagation Delay Time	t_{PHL}, t_{PLH}	5	—	100	200	ns
		10	—	55	110	
		15	—	40	85	
Transition Time	t_{THL}, t_{TLH}	5	—	100	200	ns
		10	—	50	100	
		15	—	40	80	
Input Capacitance	C_{IN}	Any Input	—	10	15	pF



CD4572UB Types

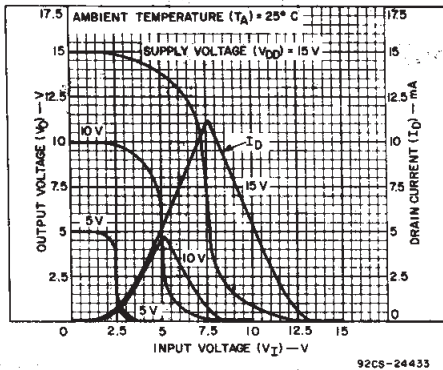


Fig. 10 - Typical inverter current and voltage transfer characteristics.

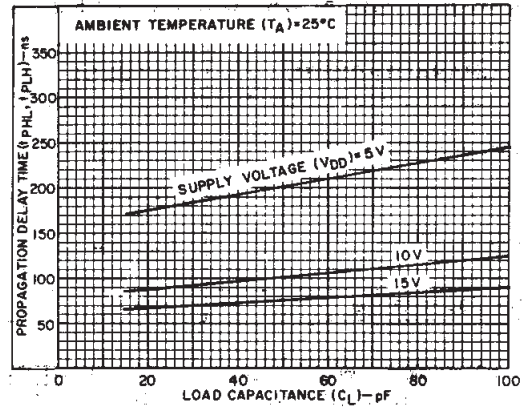


Fig. 11 - Typical propagation delay time as a function of load capacitance.

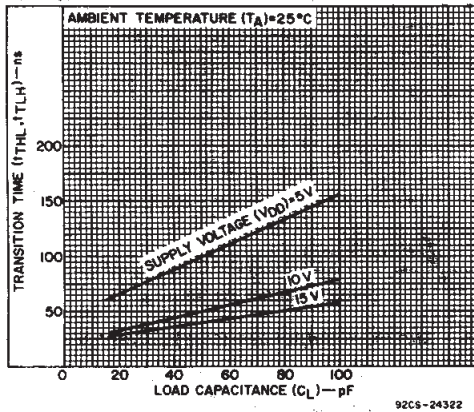


Fig. 12 - Typical transition time vs. load capacitance.

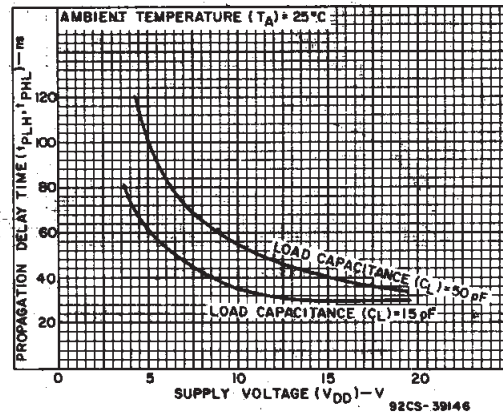


Fig. 13 - Typical propagation delay time vs. supply voltage.

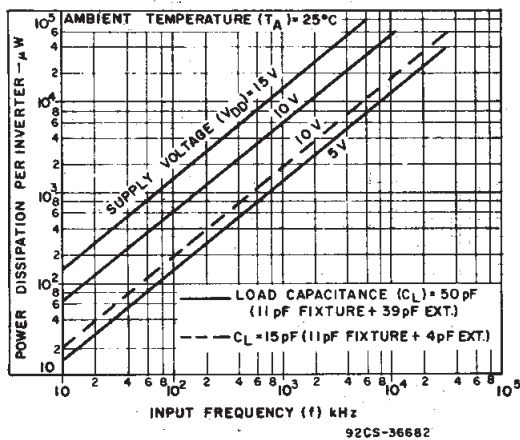


Fig. 14 - Typical dynamic power dissipation vs. frequency.

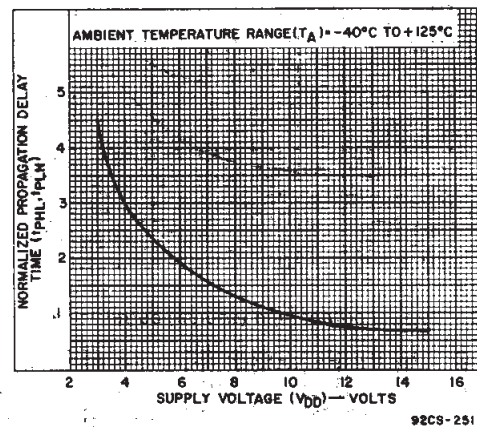
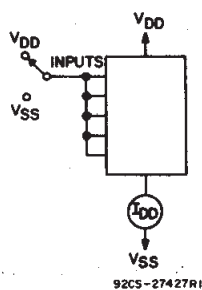


Fig. 15 - Variation of normalized propagation delay time (t_{PLH} and t_{TLH}) with supply voltage.



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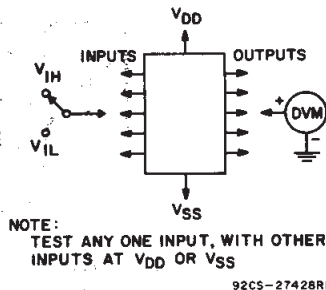


Fig. 17 - Noise immunity test circuit.

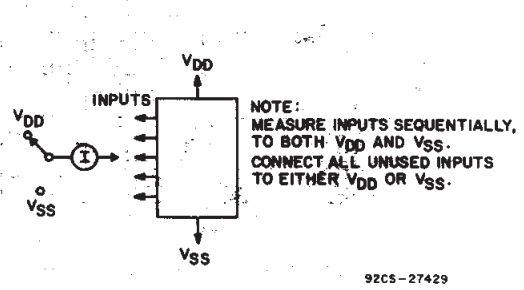


Fig. 18 - Input leakage current test circuit.

CD4572UB Types

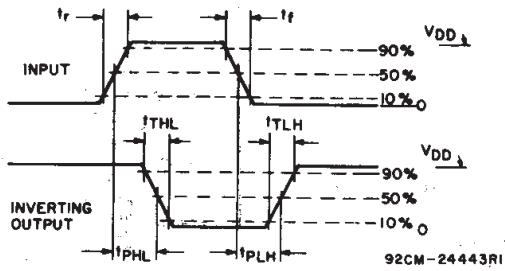
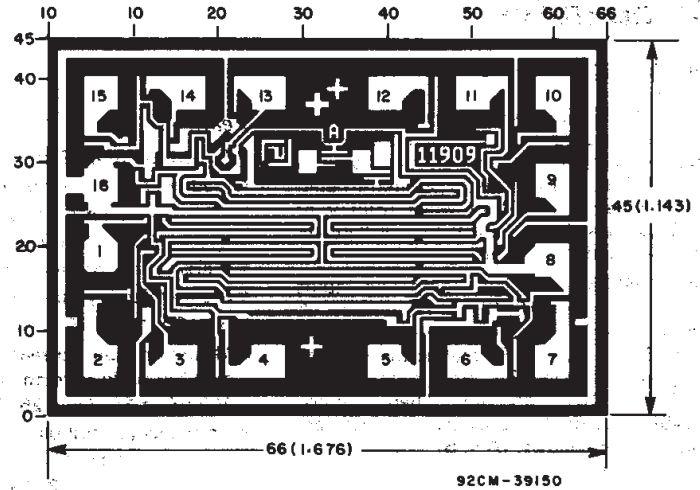


Fig. 19 - Transition times and propagation delay times, combination logic.



Dimensions and pad layout for CD4572UBH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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